

BS100C Photodiode for Visible Light

T-41-51

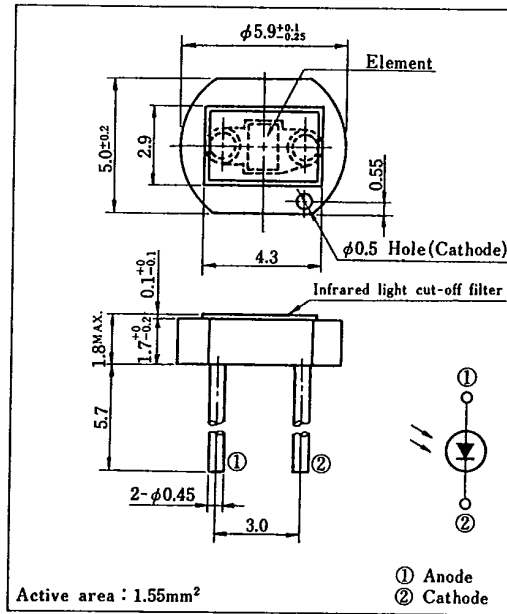
Features

- Wide dynamic range
(Capable of $E_v = 10^{-3} \sim 10^4 \ell x$ range measurement)
- Low dark current
(I_d : MAX. $10^{-11} A$ at $V_R = 1V$)
- Infrared light cut-off type

Applications

- AE (automatic exposure) system and ES (electronic shutter) system for cameras
- Precise optical instruments

Outline Dimensions (Unit : mm)



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Absolute Maximum Ratings

($T_a = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Operating temperature	T_{opr}	-20 ~ +60	$^\circ C$
Storage temperature	T_{stg}	-30 ~ +80	$^\circ C$
*1 Soldering temperature	T_{sol}	260	$^\circ C$

*1 For 5 seconds

Electro-optical Characteristics

($T_a = 25^\circ C$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
**Short circuit current	I_{sc}	$E_v = 100 \ell x$	0.14	0.16	0.21	μA
**Short circuit current temperature coefficient	β_T	$E_v = 100 \ell x$	—	0.02	0.07	%/ $^\circ C$
Dark current	I_d	$V_R = 1V$	—	3×10^{-12}	10^{-11}	A
Dark current temperature coefficient	α_T	$V_R = 1V$	—	3.5	5.0	times/ $10^\circ C$
Terminal capacitance	C_t	$V_R = 0, f = 1MHz$	—	—	500	pF
Peak sensitivity wavelength	λ_p		500	560	600	nm
**Spectral sensitivity infrared radiation ratio	ΔI_R		—	6	10	%

*2 E_v : Illuminance by CIE standard light source A (tungsten lamp)

*3 $\Delta I_R = \frac{I_{sc}(\lambda \geq 700nm)}{I_{sc}(\text{full wavelength})} \times 100\%$

Fig. 1 Short Circuit Current vs. Illuminance

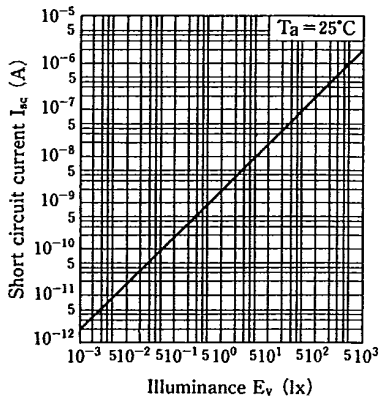


Fig. 2 Short Circuit Current vs. Ambient Temperature

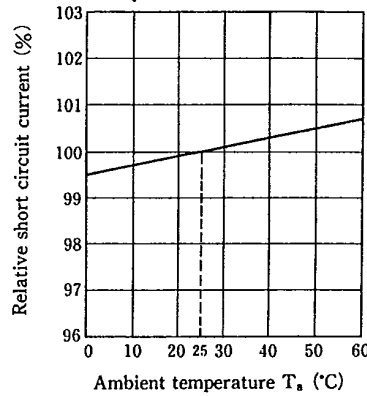


Fig. 3 Dark Current vs. Reverse Voltage

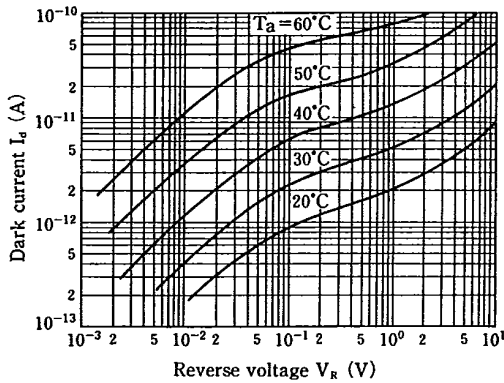


Fig. 4 Spectral Sensitivity

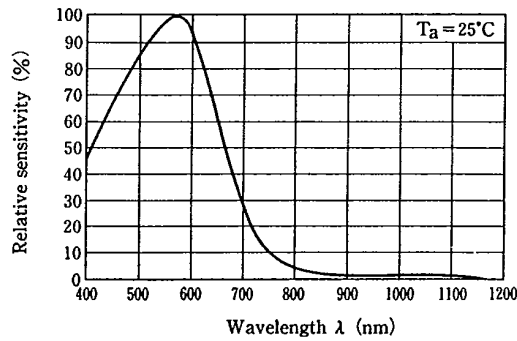
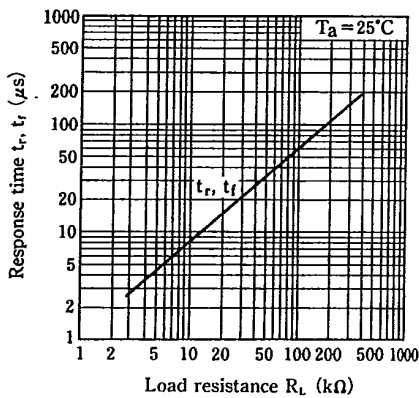


Fig. 5 Response Time vs. Load Resistance



Test Circuit for Response Time

